

IN THE CLAIMS:

1-9. (Withdrawn)

10. (Cancelled)

11-37. (Cancelled)

Please add new claims 38-59 as follows.

38. (New) A method for fabricating a semiconductor device, the method comprising

the steps of:

a) forming a lower electrode on a substrate;

b) annealing the lower electrode in a reducing atmosphere that contains impurity (new) + atoms;

c) forming a capacitive insulating film on the lower electrode after the step b); and

(✓) d) forming an upper electrode on the capacitive insulating film,

new + { wherein the impurity atoms are introduced into the lower electrode in the step b).

39. (New) The method of Claim 38, wherein the impurity atoms are hydrogen atoms.

40. (New) The method of Claim 38, wherein the annealing process is performed in an argon atmosphere containing hydrogen.

41. (New) The method of Claim 38, further comprising steps of forming an insulating film on the substrate and forming a recess on the insulating film before the step a), wherein the lower electrode is formed in the recess in the step b).

42. (New) The method of Claim 40, further comprising steps of forming an insulating film on the substrate and forming a recess in the insulating film before the step a), wherein the lower electrode is formed in the recess in the step b).

43. (New) The method of Claim 38, wherein the lower electrode has a thickness of 100 nm or less at the thinnest part thereof.

44. (New) The method of Claim 38, wherein the capacitive insulating film is formed in an oxidizing atmosphere in the step c).

45. (New) The method of Claim 38 , further comprising a step of crystallizing the capacitive insulating film by a heat treatment after the step c ) and before the step d).

46. (New) The method of Claim 38, wherein the lower electrode is made of a noble metal.

47. (New) The method of Claim 38 , wherein the lower electrode is made of a refractory metal.

48. (New) The method of Claim 38 , wherein the lower electrode is composed of Pt.

49. (New) The method of Claim 38, wherein the lower electrode is composed of Ir.

50. (New) The method of Claim 38, wherein the lower electrode is composed of Ru.

51. (New) The method of Claim 38, wherein the lower electrode is composed of Rh.

52. (New) The method of Claim 38, wherein the capacitive insulating film is an insulating film made of an oxide.

53. (New) The method of Claim 38, wherein the capacitive insulating film is composed of BST.

54. (New) The method of Claim 38, wherein the capacitive insulating film is composed of SBT.

55. (New) The method of Claim 38, wherein the capacitive insulating film is composed of PZT.

56. (New) The method of Claim 38, wherein the capacitive insulating film is composed of Ta<sub>2</sub>O<sub>5</sub>.

57. (New) The method of Claim 38, wherein the lower electrode is composed of Ru and the capacitive insulating film is composed of  $Ta_2O_5$ .

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58. (New) The method of Claim 38, wherein the lower electrode is composed of Ir and the capacitive insulating film is composed of SBT.

59. (New) The method of Claim 38, wherein the lower electrode is composed of Ir and the capacitive insulating film is composed of PZT.

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